

Vladimir A Volodin

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

235
papers

1,865
citations

22
h-index

31
g-index

272
ext. papers

2,188
ext. citations

1.5
avg, IF

4.85
L-index

#	Paper	IF	Citations
235	Nanostructuring of CVD graphene by high-energy heavy ions. <i>Diamond and Related Materials</i> , 2022 , 123, 108880	3.5	2
234	Formation of germanium nanocrystals and amorphous nanoclusters in GeSiOx films using electron beam annealing. <i>Vacuum</i> , 2022 , 197, 110796	3.7	1
233	Interaction of low-fluence femtosecond laser pulses with a composite layer containing Ge nanoclusters: A novel type of nanofoam formation. <i>Journal of Laser Applications</i> , 2022 , 34, 022002	2.1	0
232	Atomic Structure and Optical Properties of CaSi ₂ Layers Grown on CaF ₂ /Si Substrates. <i>Semiconductors</i> , 2021 , 55, 808	0.7	0
231	Synthesis of High-Purity Basic Bismuth(III) Succinate as a Pharmaceutical Substance. <i>Russian Journal of Applied Chemistry</i> , 2021 , 94, 911-919	0.8	
230	Optical properties of GeO[SiO] and GeO[SiO ₂] solid alloy layers grown at low temperature. <i>Optical Materials</i> , 2021 , 122, 111736	3.3	1
229	Crystal structure of thin CaSi ₂ films grown by radiation-induced epitaxy. <i>Journal of Crystal Growth</i> , 2021 , 562, 126080	1.6	1
228	Anisotropy of optical phonons in biaxially stressed zinc-blende- and diamond-type semiconductors and alloys. <i>Physica B: Condensed Matter</i> , 2021 , 614, 413008	2.8	1
227	Laser annealing of epitaxial CaF ₂ films on Si. <i>Thin Solid Films</i> , 2021 , 735, 138898	2.2	
226	Synthesis of Si nanoparticle chains and nanowhiskers by the monosilane decomposition in an adiabatic process during cyclic compression. <i>Powder Technology</i> , 2021 , 394, 996-1003	5.2	
225	Electron-Beam Crystallization of Thin Films of Amorphous Silicon Suboxide. <i>Technical Physics Letters</i> , 2021 , 47, 263-265	0.7	
224	Atomic Structure and Optical Properties of Plasma Enhanced Chemical Vapor Deposited SiCOH Low-k Dielectric Film. <i>Optics and Spectroscopy (English Translation of Optika i Spektroskopiya)</i> , 2021 , 129, 645-651	0.7	2
223	Vertical Ordering of Amorphous Ge Nanoclusters in Multilayer a-Ge/a-Si:H Heterostructures. <i>Technical Physics Letters</i> , 2021 , 47, 609-612	0.7	
222	On the Formation of Amorphous Ge Nanoclusters and Ge Nanocrystals in GeSixOy Films on Quartz Substrates by Furnace and Pulsed Laser Annealing. <i>Semiconductors</i> , 2020 , 54, 322-329	0.7	3
221	Negative and Positive Photoconductivity and Memristor Effect in Alloyed GeO[SiO] Films Containing Ge Nanoclusters. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 2000165	2.5	7
220	High-Temperature PIN Diodes Based on Amorphous Hydrogenated Silicon-Carbon Alloys and Boron-Doped Diamond Thin Films. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900247	1.3	0
219	Radiation-Induced epitaxial CaSi ₂ film growth at the molecular-beam epitaxy of CaF ₂ on Si. <i>Materials Letters</i> , 2020 , 268, 127554	3.3	3

218	Effect of Interfaces and Thickness on the Crystallization Kinetics of Amorphous Germanium Films. <i>Semiconductors</i> , 2020 , 54, 754-758	0.7	0
217	Formation of SnO and SnO ₂ phases during the annealing of SnO(x) films obtained by molecular beam epitaxy. <i>Applied Surface Science</i> , 2020 , 512, 145735	6.7	17
216	Quantum Size Effects in Germanium Nanocrystals and Amorphous Nanoclusters in GeSixOy Films. <i>Physics of the Solid State</i> , 2020 , 62, 492-498	0.8	13
215	Electronic structure and nanoscale potential fluctuations in strongly nonstoichiometric PECVD SiO. <i>Journal of Non-Crystalline Solids</i> , 2020 , 529, 119796	3.9	4
214	Fabrication of polycrystalline silicon thin films from a-SiO _x via the inverted aluminum-induced layer exchange process. <i>Materials Letters</i> , 2020 , 261, 127086	3.3	8
213	Silicon Nanocrystals and Amorphous Nanoclusters in SiO _x and SiN _x : Atomic, Electronic Structure, and Memristor Effects 2020 ,		1
212	Raman scattering study of nanoscale Mo/Si and Mo/Be periodic multilayer structures. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 063408	2.9	6
211	Femtosecond Laser Annealing of Multilayer Thin-Film Structures Based on Amorphous Germanium and Silicon. <i>Technical Physics Letters</i> , 2020 , 46, 560-563	0.7	1
210	Chemical Vapor Deposition of Silicon Nanoparticles on the Surface of Multiwalled Carbon Nanotubes. <i>Journal of Structural Chemistry</i> , 2020 , 61, 617-627	0.9	2
209	Structure of Germanium Monoxide Thin Films. <i>Semiconductors</i> , 2020 , 54, 1555-1560	0.7	5
208	Resistive Switching in Non-Stoichiometric Germanosilicate Glass Films Containing Ge Nanoclusters. <i>Electronics (Switzerland)</i> , 2020 , 9, 2103	2.6	8
207	Infrared photoluminescence from GeO[SiO ₂] and GeO[SiO] solid alloy layers irradiated with swift heavy Xe ions. <i>Journal of Luminescence</i> , 2020 , 223, 117238	3.8	4
206	On Raman scattering cross section ratio of amorphous to nanocrystalline germanium. <i>Solid State Communications</i> , 2020 , 313, 113897	1.6	7
205	Vibrational and Light-Emitting Properties of Si/Si _{1-x} Sn _x Heterostructures. <i>JETP Letters</i> , 2019 , 109, 368-371		1
204	Memristor effect in GeO[SiO ₂] and GeO[SiO] solid alloys films. <i>Applied Physics Letters</i> , 2019 , 114, 233104	3.4	16
203	Crystallization of Amorphous Germanium Films and Multilayer a-Ge/a-Si Structures upon Exposure to Nanosecond Laser Radiation. <i>Semiconductors</i> , 2019 , 53, 400-405	0.7	12
202	Raman Scattering in InSb Spherical Nanocrystals Ion-Synthesized in Silicon-Oxide Films. <i>Semiconductors</i> , 2019 , 53, 493-498	0.7	6
201	New graphene derivative with N-methylpyrrolidone: suspension, structural, optical and electrical properties. <i>Physical Chemistry Chemical Physics</i> , 2019 , 21, 12494-12504	3.6	2

200	All Nonmetal Resistive Random Access Memory. <i>Scientific Reports</i> , 2019 , 9, 6144	4.9	17
199	Crystallization of submicron amorphous hydrogenated silicon films with different hydrogen concentration by nanosecond ruby laser irradiation. <i>Journal of Laser Applications</i> , 2019 , 31, 012006	2.1	
198	The Use of Spectral Ellipsometry and Raman Spectroscopy in Screening Diagnostics of Colorectal Cancer. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2019 , 127, 170-176	0.7	3
197	Luminescence Properties of FZ Silicon Irradiated with Swift Heavy Ions. <i>Semiconductors</i> , 2019 , 53, 1427-1430	0.7	1
196	POSSIBILITIES OF OPTICAL METHODS FOR STUDYING THE BLOOD SERUM IN THE DIAGNOSTICS OF LIVER DIFFUSE PATHOLOGY. <i>Interexpo GEO-Siberia</i> , 2019 , 8, 19-27	0.1	
195	Study of Structural Modification of Composites with Ge Nanoclusters by Optical and Electron Microscopy Methods. <i>Semiconductors</i> , 2019 , 53, 2064-2067	0.7	1
194	Nanosized Potential Fluctuations in SiO _x Synthesized by Plasma-Enhanced Chemical Vapor Deposition. <i>Physics of the Solid State</i> , 2019 , 61, 2560-2568	0.8	2
193	Electroluminescence of thin film p-i-n diodes based on a-SiC:H with integrated Ge nanoparticles. <i>EPJ Applied Physics</i> , 2019 , 88, 30302	1.1	2
192	Localization of Optical Phonons in Diamond Nanocrystals. <i>Journal of Experimental and Theoretical Physics</i> , 2019 , 129, 816-824	1	1
191	Atomic and Electronic Structures of a-SiN _x :H. <i>Journal of Experimental and Theoretical Physics</i> , 2019 , 129, 924-934	1	4
190	Light-emitting defects formed in GeO/SiO ₂ heterostructures with assistance of swift heavy ions. <i>Journal of Luminescence</i> , 2019 , 207, 209-212	3.8	7
189	New Method of Porous Ge Layer Fabrication: Structure and Optical Properties. <i>Semiconductors</i> , 2018 , 52, 628-631	0.7	1
188	Raman scattering in boron doped nanocrystalline diamond films: Manifestation of Fano interference and phonon confinement effect. <i>Solid State Communications</i> , 2018 , 276, 33-36	1.6	9
187	Raman and photoluminescence spectroscopy of SiGe layer evolution on Si(100) induced by dewetting. <i>Journal of Applied Physics</i> , 2018 , 123, 015304	2.5	19
186	Effect of annealing in oxidizing atmosphere on optical and structural properties of silicon suboxide thin films obtained by gas-jet electron beam plasma chemical vapor deposition method. <i>Vacuum</i> , 2018 , 152, 319-326	3.7	11
185	Ion-Beam Synthesis of the Crystalline Ge Phase in SiO _x N _y Films upon Annealing under High Pressure. <i>Semiconductors</i> , 2018 , 52, 268-272	0.7	
184	Influence of the Growth Temperature on the Defective Structure of the Multi-Walled Carbon Nanotubes. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700255	1.3	7
183	Optical Properties of Nonstoichiometric Tantalum Oxide TaO _x (x Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2018 , 124, 808-813	0.7	10

182	On Raman scattering cross section ratio of crystalline and microcrystalline to amorphous silicon. <i>Applied Physics Letters</i> , 2018 , 113, 023101	3.4	24
181	Nanoscale potential fluctuations in nonstoichiometric tantalum oxide. <i>Nanotechnology</i> , 2018 , 29, 425202	3.4	5
180	Aluminum-induced crystallization of silicon suboxide thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2018 , 124, 1	2.6	8
179	Atomic and Electronic Structures of Metal-Rich Noncentrosymmetric ZrOx. <i>JETP Letters</i> , 2018 , 108, 226-230	2.3	2
178	Raman shifts and photoluminescence of the InSb nanocrystals ion beam-synthesized in buried SiO ₂ layers. <i>Journal of Luminescence</i> , 2018 , 204, 656-662	3.8	2
177	On the Formation of IR-Light-Emitting Ge Nanocrystals in Ge:SiO ₂ Films. <i>Semiconductors</i> , 2018 , 52, 1178-1187	1.7	2
176	Forbidden Resonant Raman Scattering in GaAs/AlAs Superlattices: Experiment and Calculations. <i>Semiconductors</i> , 2018 , 52, 717-722	0.7	
175	Local Oscillations of Silicon-Silicon Bonds in Silicon Nitride. <i>Technical Physics Letters</i> , 2018 , 44, 424-427	0.7	6
174	Nanostructuring few-layer graphene films with swift heavy ions for electronic application: tuning of electronic and transport properties. <i>Nanoscale</i> , 2018 , 10, 14499-14509	7.7	26
173	Splitting of frequencies of optical phonons in tensile-strained germanium layers. <i>JETP Letters</i> , 2017 , 105, 327-331	1.2	14
172	Local anodic oxidation of solid GeO films: The nanopatterning possibilities. <i>Surfaces and Interfaces</i> , 2017 , 6, 56-59	4.1	5
171	Light-emitting Si nanostructures formed by swift heavy ions in a-Si:H/SiO ₂ multilayer heterostructures. <i>Materials Research Express</i> , 2017 , 4, 085001	1.7	3
170	Formation and study of p-i-n structures based on two-phase hydrogenated silicon with a germanium layer in the i-type region. <i>Semiconductors</i> , 2017 , 51, 1370-1376	0.7	5
169	Synthesis of basic bismuth(III) oxalate by precipitation from nitrate solutions. <i>Russian Journal of Applied Chemistry</i> , 2017 , 90, 1040-1046	0.8	2
168	Ge nanocrystals formed by furnace annealing of Ge(x)[SiO ₂](1-x) films: structure and optical properties. <i>Materials Research Express</i> , 2017 , 4, 075010	1.7	9
167	Optical properties of Si nanocrystals formed with laser pulse annealing. <i>Materials Today: Proceedings</i> , 2017 , 4, 11402-11405	1.4	5
166	Specific features of the ion-beam synthesis of Ge nanocrystals in SiO ₂ thin films. <i>Semiconductors</i> , 2017 , 51, 1240-1246	0.7	
165	Angular dependence of Raman scattering selection rules for long-wavelength optical phonons in short-period GaAs/AlAs superlattices. <i>Journal of Experimental and Theoretical Physics</i> , 2016 , 123, 163-168	1.8	2

164	Structure and infrared photoluminescence of GeSi nanocrystals formed by high temperature annealing of GeOx/SiO2 multilayers. <i>Materials Research Express</i> , 2016 , 3, 085019	1.7	13
163	Luminescence in GeO x films containing germanium nanoclusters. <i>Nanotechnologies in Russia</i> , 2016 , 11, 325-330	0.6	2
162	Enhanced germanium precipitation and nanocrystal growth in the Ge+ ion-implanted SiO2 films during high-pressure annealing. <i>Solid State Communications</i> , 2016 , 247, 53-57	1.6	5
161	Formation of silicon nanocrystals in SiSiO2SiSiO2 heterostructures during high-temperature annealing: Experiment and simulation. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2016 , 52, 486-495	0.6	1
160	Raman studies of phase and atomic compositions of GeSi nanosystems after pulsed annealing. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2016 , 52, 496-500	0.6	2
159	GeSi nanocrystals formed by high temperature annealing of GeO/SiO2 multilayers: structure and optical properties 2016 ,		1
158	Optical properties of p-i-n structures based on amorphous hydrogenated silicon with silicon nanocrystals formed via nanosecond laser annealing. <i>Semiconductors</i> , 2016 , 50, 935-940	0.7	7
157	Structure and optical properties of Si and SiGe layers grown on SiO2 by chemical vapor deposition. <i>Thin Solid Films</i> , 2015 , 579, 131-135	2.2	12
156	Interaction of optical and interface phonons and their anisotropy in GaAs/AlAs superlattices: Experiment and calculations. <i>Journal of Experimental and Theoretical Physics</i> , 2015 , 120, 781-789	1	6
155	Redshift of the absorption edge in tensile-strained germanium layers. <i>JETP Letters</i> , 2015 , 101, 419-421	1.2	6
154	Experimental observation of interface-phonon-plasmon mode in n-GaAs/i-GaAs heterostructure. <i>Solid State Communications</i> , 2015 , 224, 21-23	1.6	1
153	Highly conductive indium nanowires deposited on silicon by dip-pen nanolithography. <i>Journal of Applied Physics</i> , 2015 , 117, 145305	2.5	
152	Infrared photoluminescence from GeSi nanocrystals embedded in a germanium silicate matrix. <i>Journal of Experimental and Theoretical Physics</i> , 2015 , 121, 1076-1081	1	8
151	Applying an improved phonon confinement model to the analysis of Raman spectra of germanium nanocrystals. <i>Journal of Experimental and Theoretical Physics</i> , 2014 , 118, 65-71	1	44
150	Functionalization of graphene and few-layer graphene films in an hydrofluoric acid aqueous solution. <i>Nanotechnologies in Russia</i> , 2014 , 9, 51-59	0.6	23
149	Raman scattering in PbTe and PbSnTe films: In situ phase transformations. <i>Semiconductors</i> , 2014 , 48, 173-177	0.7	5
148	Optical properties of tensile-strained and relaxed Ge films grown on InGaAs buffer. <i>Journal of Applied Physics</i> , 2014 , 115, 053518	2.5	13
147	Effect of hydrostatic pressure during the annealing of silicon-on-insulator films implanted with a high hydrogen-ion dose. <i>Semiconductors</i> , 2014 , 48, 1303-1307	0.7	1

146	Electron-phonon interaction and Raman scattering in doped GaAs/AlAs superlattices. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2014 , 50, 271-275	0.6	1
145	Phase separation as a basis for the formation of light-emitting silicon nanoclusters in SiO _x films irradiated with swift heavy ions. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2014 , 50, 292-297	0.6	0
144	Anisotropy of long-wavelength optical phonons in GaAs/AlAs superlattices. <i>JETP Letters</i> , 2014 , 99, 396-399	0.9	9
143	Comparison of various methods for transferring graphene and few layer graphene grown by chemical vapor deposition to an insulating SiO ₂ /Si substrate. <i>Semiconductors</i> , 2014 , 48, 804-808	0.7	15
142	Optical phonons as a probe to determine both composition and strain in In _x Al _(1-x) As quantum dots embedded in an AlAs matrix. <i>Europhysics Letters</i> , 2014 , 105, 16003	1.6	10
141	Formation of Si nanocrystals in SiO _x , SiO _x :C:H films and Si/SiO ₂ multilayer nano-heterostructures by pulse laser treatments 2014 ,		1
140	Formation of Ge and GeSi nanocrystals in GeO _x /SiO ₂ multilayers. <i>Journal Physics D: Applied Physics</i> , 2013 , 46, 275305	3	26
139	Crystallization induced by thermal annealing with millisecond pulses in silicon-on-insulator films implanted with high doses of hydrogen ions. <i>Semiconductors</i> , 2013 , 47, 606-611	0.7	1
138	Layered structures based on hydrogenated graphene with high carrier mobility. <i>Nanotechnologies in Russia</i> , 2013 , 8, 621-626	0.6	3
137	Formation and structural features of silicon quantum dots in germanium. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2013 , 49, 434-439	0.6	1
136	Quantitative analysis of hydrogen in amorphous silicon using Raman scattering spectroscopy. <i>Journal of Raman Spectroscopy</i> , 2013 , 44, 1760-1764	2.3	55
135	Influence of irradiation with swift heavy ions on multilayer Si/SiO ₂ heterostructures. <i>Semiconductors</i> , 2013 , 47, 358-364	0.7	1
134	Functionalization of graphene and few-layer graphene with aqueous solution of hydrofluoric acid. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2013 , 52, 106-111	3	38
133	Improved model of optical phonon confinement in silicon nanocrystals. <i>Journal of Experimental and Theoretical Physics</i> , 2013 , 116, 87-94	1	51
132	Photoluminescence and Raman scattering of silicon nanopowders. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2013 , 77, 1087-1090	0.4	
131	Laser pulse crystallization and optical properties of Si/SiO ₂ and Si/Si ₃ N ₄ multilayer nano-heterostructures 2013 ,		1
130	Radiative recombination in silicon-on-insulator layers implanted with high dose of H ⁺ ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012 , 282, 73-75	1.2	
129	Light-emitting Si nanostructures formed by swift heavy ions in stoichiometric SiO ₂ layers. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012 , 282, 68-72	1.2	8

128	Evolution of silicon nanoclusters and hydrogen in SiN _x :H films: Influence of high hydrostatic pressure under annealing. <i>Thin Solid Films</i> , 2012 , 520, 6207-6214	2.2	10
127	Formation of conductive layers inside diamond by hydrogen ion implantation and subsequent thermal treatment at low or high pressures. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2012 , 76, 577-581	0.4	1
126	Folding of acoustic-phonon modes in GaAs/AlAs (311)A superlattices in the direction perpendicular to nanofacets. <i>JETP Letters</i> , 2012 , 95, 70-73	1.2	4
125	Anomalous temperature dependence of photoluminescence in GeO _x films and GeO _x /SiO ₂ nano-heterostructures. <i>JETP Letters</i> , 2012 , 95, 424-428	1.2	9
124	Lowest-lying vibrational signatures in corticosteroids studied by terahertz time-domain and Raman spectroscopies. <i>Vibrational Spectroscopy</i> , 2012 , 62, 238-247	2.1	15
123	Lattice dynamics of bismuth tellurohalides. <i>Physical Review B</i> , 2012 , 86,	3.3	31
122	SiGe quantum rings on the Si(100) surface. <i>Russian Microelectronics</i> , 2012 , 41, 485-488	0.5	
121	Tunable properties of few-layer graphene-N-methylpyrrolidone hybrid structures. <i>Nanotechnology</i> , 2012 , 23, 315601	3.4	10
120	Enhanced formation of Ge nanocrystals in Ge : SiO ₂ layers by swift heavy ions. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 285302	3	7
119	Quantum-confinement effect in silicon-on-insulator films implanted with high doses of hydrogen ions. <i>Semiconductors</i> , 2012 , 46, 1286-1290	0.7	1
118	Vibrations in binary and ternary topological insulators: First-principles calculations and Raman spectroscopy measurements. <i>Physical Review B</i> , 2012 , 86,	3.3	68
117	Crystallization of hydrogenated amorphous-nanocrystalline silicon films under high-pressure annealing. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1487-1489		
116	Experience in depositing carbon coatings by the gas-jet method. <i>Journal of Engineering Physics and Thermophysics</i> , 2012 , 85, 101-109	0.6	3
115	Crystallization of amorphous Si nanoclusters in SiO(x) films using femtosecond laser pulse annealings. <i>Journal of Nanoscience and Nanotechnology</i> , 2012 , 12, 8694-9	1.3	10
114	Vibrational Spectroscopy of Chemical Species in Silicon and Silicon-Rich Nitride Thin Films. <i>International Journal of Spectroscopy</i> , 2012 , 2012, 1-5		23
113	Femtosecond pulse crystallization of thin amorphous hydrogenated films on glass substrates using near ultraviolet laser radiation. <i>JETP Letters</i> , 2011 , 93, 603-606	1.2	7
112	Formation of silicon nanocrystals in SiN _x film on PET substrates using femtosecond laser pulses. <i>Technical Physics Letters</i> , 2011 , 37, 622-625	0.7	4
111	Raman scattering spectroscopy of inclusions of carbon in Al ₂ O ₃ films and its solid solutions with HfO ₂ . <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2011 , 110, 55-59	0.7	3

110	Crystallization of hydrogenated amorphous silicon films by exposure to femtosecond pulsed laser radiation. <i>Semiconductors</i> , 2011 , 45, 265-270	0.7	13
109	Formation of light-emitting nanostructures in layers of stoichiometric SiO ₂ irradiated with swift heavy ions. <i>Semiconductors</i> , 2011 , 45, 1311-1316	0.7	3
108	Anisotropy of phonon-plasmon modes in GaAs/AlAs(311) superlattices. <i>Physics of the Solid State</i> , 2011 , 53, 404-406	0.8	6
107	Oxidation kinetics of a silicon surface in a plasma of oxygen with inert gases. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2011 , 47, 459-464	0.6	3
106	Extremely high response of electrostatically exfoliated few layer graphene to ammonia adsorption. <i>Nanotechnology</i> , 2011 , 22, 285502	3.4	20
105	Visible Light-Emitting Hydrogenated Nanocrystalline Silicon-on-Insulator Films: Formation and Properties. <i>Solid State Phenomena</i> , 2011 , 178-179, 453-458	0.4	
104	Creation of Nanoperiodical Multilayer Si/SiO ₂ Structures in Plasma-Chemical Reactor of Induction Type and Their Properties. <i>Vestnik Novosibirskogo Gosudarstvennogo Universiteta Seriya Fizika</i> , 2011 , 6, 107-114		
103	Terahertz time-domain spectroscopy of testosterone, estradiol and estriol 2010 ,		1
102	Vibrational spectra of corticosteroid hormones in the terahertz range 2010 ,		2
101	X-ray and infrared spectroscopy of layers produced by cosputtering of spatially separated SiO ₂ and Si sources. <i>Semiconductors</i> , 2010 , 44, 531-536	0.7	7
100	Formation and crystallization of silicon nanoclusters in SiN _x :H films using femtosecond pulsed laser annealings. <i>Semiconductors</i> , 2010 , 44, 1611-1616	0.7	5
99	Modification of germanium nanoclusters in GeO _x films during isochronous furnace and pulse laser annealing. <i>Technical Physics Letters</i> , 2010 , 36, 439-442	0.7	6
98	Femtosecond laser induced formation of Si nanocrystals and amorphous Si clusters in silicon-rich nitride films. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 1820-1823	3	20
97	Anharmonicity of Phonons in Silicon: Raman Spectroscopy Study. <i>Vestnik Novosibirskogo Gosudarstvennogo Universiteta Seriya Fizika</i> , 2010 , 5, 48-55		
96	Temperature Dynamics for Low-Frequency Raman Spectra of Progesterone, 17β-Hydroxyprogesterone and Cortisone. <i>Vestnik Novosibirskogo Gosudarstvennogo Universiteta Seriya Fizika</i> , 2010 , 5, 168-172		
95	Variation in optical-absorption edge in SiN _x layers with silicon clusters 2010 , 42, 202		
94	Effect of high-power nanosecond and femtosecond laser pulses on silicon nanostructures 2010 , 42, 183		
93	Charge spectroscopy of Si nanocrystallites embedded in a SiO ₂ matrix. <i>Journal of Applied Physics</i> , 2009 , 106, 064306	2.5	12

92	Temperature-Dependent PL Intensity in FLA-Synthesized and Hydrogen-Modified Silica Layers with Silicon Nanocrystals. <i>ECS Transactions</i> , 2009 , 16, 105-111	1	2
91	Anisotropic Strain Induced by Anisotropic Heating Engineering for Silicon Nanocrystals in SiO ₂ . <i>Solid State Phenomena</i> , 2009 , 156-158, 523-528	0.4	3
90	Quasi-direct optical transitions in Ge nanocrystals embedded in GeO ₂ matrix. <i>JETP Letters</i> , 2009 , 89, 76-79	1.2	4
89	Experimental discovery of the anisotropy of phonon-plasmon modes in GaAs/AlAs(100) superlattices. <i>JETP Letters</i> , 2009 , 89, 419-421	1.2	4
88	Ellipsometry of GeO ₂ films with Ge nanoclusters: Influence of the quantum-size effect on refractive index. <i>Optics and Spectroscopy (English Translation of Optika i Spektroskopiya)</i> , 2009 , 106, 436-440	0.7	4
87	Scanning-probe-induced local decomposition of solid germanium monoxide films: The nano-patterning of germanium. <i>Journal of Surface Investigation</i> , 2009 , 3, 773-780	0.5	2
86	Structure and optical properties of SiN _x :H films with Si nanoclusters produced by low-frequency plasma-enhanced chemical vapor deposition. <i>Semiconductors</i> , 2009 , 43, 1514-1520	0.7	14
85	The decomposition mechanism of metastable solid GeO film 2009 ,		1
84	The modification of Si nanocrystallites embedded in a dielectric matrix by high energy ion irradiation. <i>Nanotechnology</i> , 2009 , 20, 095205	3.4	10
83	Temperature Dependence of the Photoluminescence Intensity in Si ₃ +xN ₄ :H Films with Amorphous Si Nanoclusters: Evidence for Two Processes Involved in the Nonradiative Relaxation of Photoexcitations. <i>ECS Transactions</i> , 2009 , 25, 35-42	1	2
82	Crystallization of Clusters of Amorphous Silicon in Si _x Films on Glass Substrates Using Nanosecond Pulse Impacts of Excimer KrF Laser. <i>Vestnik Novosibirskogo Gosudarstvennogo Universiteta Seriya Fizika</i> , 2009 , 4, 47-52		
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2 Silicon nanocluster in silicon nitride: photoluminescence, Raman scattering and ESR studies 1

1 Graphene/Hexagonal Boron Nitride Composite Nanoparticles for 2D Printing Technologies.
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